## 2SC5383

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON NPN EPITAXIAL TYPE(Ultra super mini type)

#### **DESCRIPTION**

2SC5383 is a ultra super mini package resin sealed silicon NPN epitaxial transistor,

It is designed for low frequency voltage application.

### **FEATURE**

Small collector to emitter saturation voltage.

VCE(sat)=0.3V max(@lc=100mA,IB=10mA)

Excellent linearity of DC forward gain.

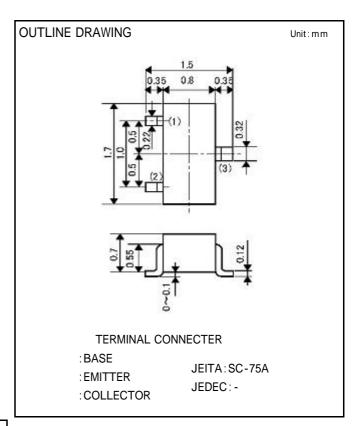
Ultra super mini package for easy mounting

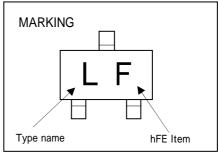
### **APPLICATION**

For Hybrid IC,small type machine low frequency voltage Amplify application.

### MAXIMUM RATINGS (Ta=25 )

Parameter	Ratings	Unit
Collector to Base voltage	50	V
Collector to Emitter voltage	50	V
Emitter to Base voltage	6	V
Collector current	200	mA
Collector dissipation	150	mW
Junction temperature	+ 150	
Storage temperature	-55 ~ + 150	
	Collector to Base voltage Collector to Emitter voltage Emitter to Base voltage Collector current Collector dissipation Junction temperature	Collector to Base voltage 50  Collector to Emitter voltage 50  Emitter to Base voltage 6  Collector current 200  Collector dissipation 150  Junction temperature + 150





### ELECTRICAL CHARACTERISTICS (Ta=25 )

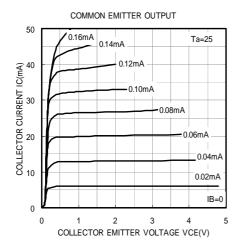
Parameter	Symbol	Test conditions	Limits			Unit
	Symbol	rest conditions	Min	Тур	Max	Offic
C to E break down voltage	V(BR)ceo	$I_{C}=100 \mu A$ ,R $_{BE}=$	50	-	-	V
Collector cut off current	ICBO	$V_{CB}$ =50V, $I_{E}$ =0mA	-	-	0.1	μΑ
Emitter cut off current	IEBO	$V_{EB}$ =6V, $I_{C}$ =0mA	ı	-	0.1	μΑ
DC forward current gain	hFE	$V_{CE}=6V, I_{C}=1mA$	150	-	500	
DC forward current gain	hFE	$V_{CE}$ =6V, $I_{C}$ =0.1mA	90	-	-	
C to E Saturation Vlotage	VCE(sat)	I <sub>C</sub> =100mA ,I <sub>B</sub> =10mA	ı	-	0.3	V
Gain bandwidth product	fT	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	i	200	-	MHz
Collector output capacitance	Cob	$V_{CB}=6V, I_{E}=0, f=1MHz$	-	2.5	-	pF
Noise figure	NF	$V_{CE}=6V, I_{E}=-0.1mA, f=1kHz, RG=2k$	-	-	15	dB

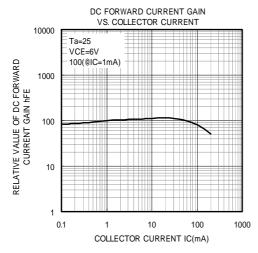
) It shows hFE classification at right table.

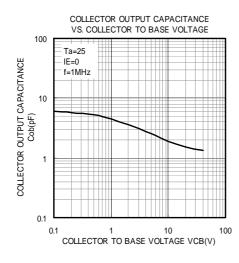
Item	Е	F	
hFE Item	150 ~ 300	250 ~ 500	

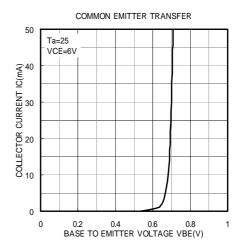
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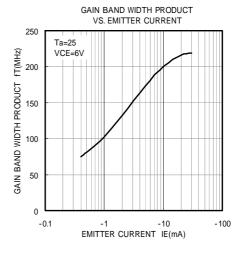
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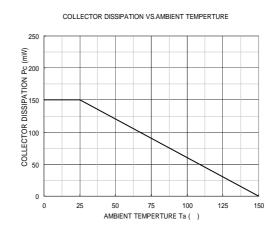






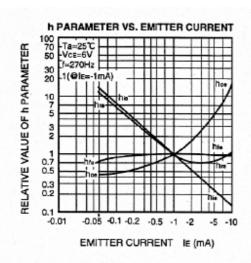


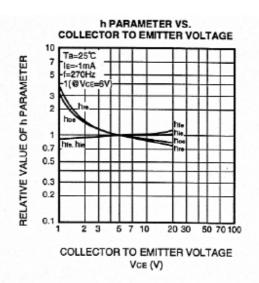




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## COMMON EMITTER h PARAMETER (TYPICAL VALUE)

Symbol	Parameter	Test conditions	Limits	Unit
hie	Closed loop small signal input impedance	Ta=25°C	8.5	kΩ
hre	Open loop small signal reverse voltage amplification factor	VCE=6V	0.1	×10-3
hte	Closed loop small signal forward current amplification factor	IE=-1mA f=270Hz	300	
hoe	Open loop small signal output admittance		5.5	μS



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